

Consciously Constructing Heterojunction or Direct Z-Scheme Photocatalysts by Regulating Electron Flow Direction

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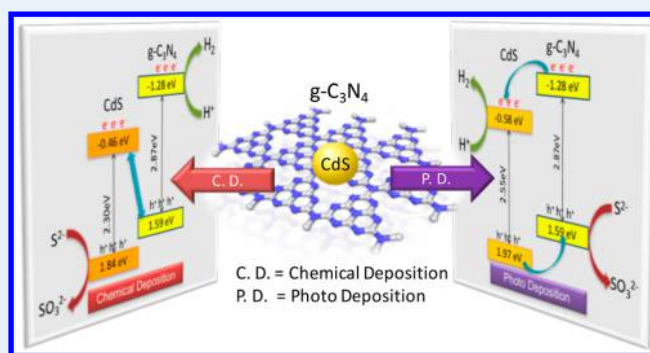
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Supporting Information

ABSTRACT: Heterojunction and direct Z-scheme nanostructures are two typical representatives of an efficient photocatalyst, which is composed of two semiconductors. However, it is a great challenge to construct each of them on purpose. The photodeposition technique can be a potentially powerful tool to regulate the electron flow direction for constructing these nanostructures. In this report, CdS nanoparticles were deposited on the g-C₃N₄ nanosheets by photodeposition and chemical deposition methods for comparison. In the photodeposition case, PL and charge flow tracking demonstrate that a type II heterojunction is constructed because CdS is selectively deposited at the electron transfer site of g-C₃N₄, which leads to the photoexcited electron from g-C₃N₄ tending to transfer to CdS in the composites. In the latter, the CdS is randomly deposited onto the g-C₃N₄ nanosheets through chemical deposition. There is no preferred site for deposition or charge transfer in the composite. The results illustrate that the electron of CdS tends to recombine with the hole from g-C₃N₄. The direct Z-scheme is predominant for the CdS/g-C₃N₄ prepared by the chemical deposition route. Furthermore, the photocatalytic performance and stability also confirm the above results. On the of these, we can deduce that the photodeposition method can be used to regulating the electron transfer route. We expect this report to shed light on the rational design of heterojunction or direct Z-scheme type composites.

KEYWORDS: type II heterojunction, direct Z-scheme, photodeposition, CdS, g-C₃N₄, composite photocatalyst



INTRODUCTION

Photocatalytic water splitting has attracted substantial attention as a potential system for clean hydrogen energy.^{1–3} To utilize solar energy efficiently, photocatalysts are highly expected to possess broadly visible light adsorption and high charge separation efficiency.^{4–9} Currently, single-photocatalyst systems, such as TiO₂, g-C₃N₄, and sulfide compounds, hardly satisfy these requirements for full-spectrum water splitting.^{10,11} Constructing composite materials has been put forward to further broaden the light adsorption and enhance the charge separation of the photocatalyst.^{12,13} A heterojunction forms at the interface between two semiconductors with unequal band gaps by physical contact with each other. In a type II heterojunction, the excited electrons and holes kinetically flow downward and upward, respectively.¹⁴ This leads to the electron and hole spatial separation and enhances the charge separation efficiency. A Z-scheme type photocatalyst is another

composite system for water splitting to mimic the natural photosynthesis process, in which the excited electron of photosystem II (PSII) is transferred toward photosystem I (PSI) and recombined with the hole on it with the aid of an electron-transfer mediator. The excited electrons of PSI and the holes of PSII with high reduction and oxidation capability are left and used for reduction and oxidation reactions.^{15,16} The electron mediators could be ionic type redox pairs such as IO₃[−]/I[−], Fe^{3+/2+}, and Co(bpy)₃^{3+/2+} or conductor-like metal nanoparticles and reduced graphene oxide (RGO).^{17–25} Recently, a new type of Z-scheme system without any redox mediator was proposed and called a direct Z-scheme.^{26–28} Two semiconductors are placed together just as for a type II

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heterojunction; however, the charge transfer route follows the Z-scheme, in which the excited electron of one semiconductor recombines with the hole of another semiconductor in the direct Z-scheme. Notably, the backward reactions and the shielding effect of a Z-scheme system with redox mediators are primarily suppressed because of the absence of redox mediators.²⁵

Bewilderingly, both type II heterojunction and direct Z-scheme catalysts are composed by simply contacting two semiconductors together. Until now, it is still an open question and challenge to consciously construct type II heterojunction and/or direct Z-scheme catalysts. Photodeposition is a common method to deposit the cocatalyst Pt onto a catalyst to enhance the electron transfer toward Pt nanoparticles.²⁹ Thus, the photodeposition technique could be used to regulate the electron transfer direction. Thus, we proposed constructing these two systems by regulating excited electron flow direction, since they have different electron transfer routes. To prove this concept, we synthesized CdS/g-C₃N₄ composites by a photodeposition route. For comparison, CdS/g-C₃N₄ composites were also synthesized via a chemical deposition route. In the case of Photodeposition, CdS was selectively formed on the site, where the photo excited electron prefers transferring to, because the sulfur was reduced to form sulfide at the same site. Thus, the photoexcited electron of g-C₃N₄ prefers to be transferred to CdS in the CdS/g-C₃N₄ composite. The PL and electron flow tracking experiment results confirm the formation of a type II heterojunction in the composites. In the case of chemical deposition, CdS was randomly deposited onto the g-C₃N₄ nanosheets in the chemical deposition. There is no preference for photogenerated electron transfer. The PL and charge flow tracking experiment results indicate that the direct Z-scheme type takes a dominant place in this composite. The photocatalytic performance and stability further demonstrate that the holes are transferred from CdS to g-C₃N₄, which effectively prevent CdS from photocorrosion, in the composites prepared via the photodeposition route. On the other hand, the recombination takes place between an electron from CdS and a hole from g-C₃N₄ in the direct Z-scheme type composite. The hole left at CdS potentially oxidizes the catalyst and deteriorates the performance of the catalyst. This report opens the door to the rational design of type II heterojunction and/or Z-scheme catalysts by controlling the electron flow direction using different synthesis routes.

RESULTS AND DISCUSSION

Typically, g-C₃N₄ nanosheets were prepared through the pyrolysis of urea.³⁰ Photodeposition of CdS onto g-C₃N₄ nanosheets (p-CSCN) was synthesized in an ethanol dispersion of 0.2 g of g-C₃N₄ containing 2 mmol of S powder and 8 mmol of Cd(NO₃)₂; the deposition temperature was set at 4, 25, and 50 °C for 2 h to obtain p-CSCN-4, -25, and -50, respectively.³¹ The S first was photoreduced into S²⁻ under light irradiation by g-C₃N₄. CdS immediately forms at the S²⁻ site due to the presence of excess Cd²⁺. The chemical deposition of CdS/g-C₃N₄ composites (c-CSCN) was achieved by a hydrothermal route³² by adding 0.5 g of g-C₃N₄ to a Cd(NO₃)₂ and thioacetamide (TAA) aqueous solution at 160 °C for 5 h. The amount of CdS was tuned by Cd(NO₃)₂ from 0.035 to 0.525 mmol to obtain c-CSCN-1–15% samples. After optimization (Figures S1–S5 in the Supporting Information), p-CSCN-25 and c-CSCN-10% were chosen as typical samples for further comparative investigation of p-CSCN and c-CSCN.

Figure 1 shows typical scanning electron microscopy (SEM) and TEM images of g-C₃N₄, p-CSCN-25, and c-CSCN-10%

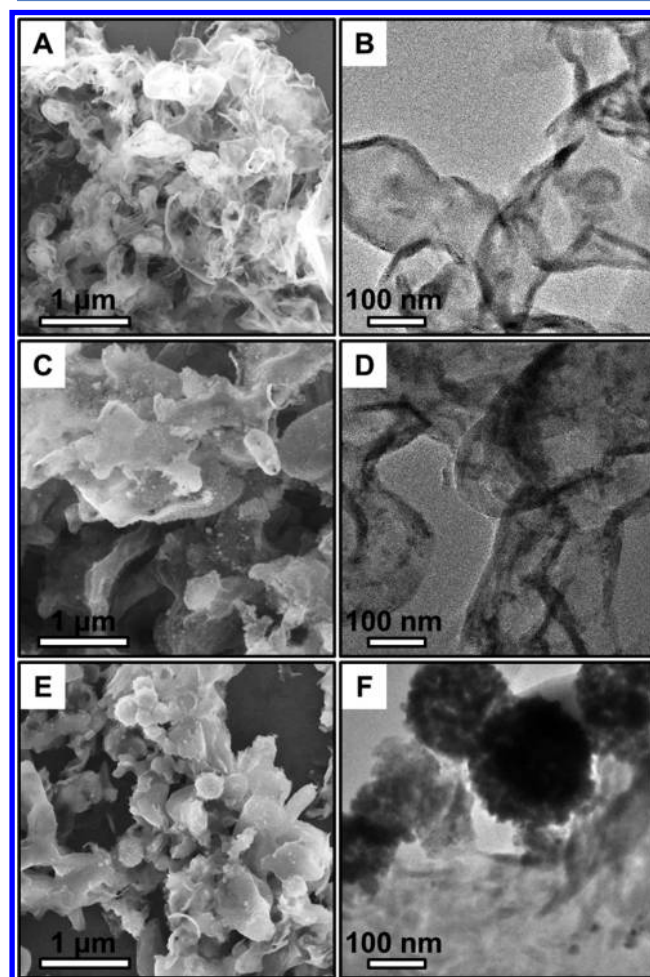


Figure 1. Morphologies of g-C₃N₄, p-CSCN-25, and c-CSCN-10% samples: scanning electron microscopy (SEM) and transmission electron microscopy (TEM) images of g-C₃N₄ (A, B), p-CSCN-25 (C, D), and c-CSCN-10% (E, F).

photocatalyst composites. g-C₃N₄ exhibits a nanosheet morphology with a high specific surface area ($\sim 93 \text{ m}^2 \text{ g}^{-1}$, Figure S6 and Table S1). The specific surface areas slightly decrease to $76 \text{ m}^2 \text{ g}^{-1}$ after loading of CdS due to the stacking of nanosheets. In the case of p-CSCN-25, CdS nanoparticles were individually deposited on the surface of g-C₃N₄ (Figure 1C). The TEM image displays CdS nanoparticles of $\sim 4.0 \text{ nm}$ average size on the g-C₃N₄ nanosheets, resulting in CdS having a relatively large band gap and narrow visible light adsorption.³³ Figure 1E,F presents the SEM and TEM images of c-CSCN-10%, which show many large spherical nanoparticle aggregates ($\sim 200 \text{ nm}$ in diameter) on the surface of g-C₃N₄ in addition to small particles with a size of $\sim 20 \text{ nm}$. SEM images of c-CSCN series samples, as shown in Figure S7, disclose that most of the CdS nanoparticles tend to separately scatter on the surface when the amount of CdS is low ($\sim 1\%$). However, CdS nanoparticles tend to aggregate and form large spheres on overloading. This may be the reason the photocatalytic performance of c-CSCN-15% is lower than that of c-CSCN-10%.

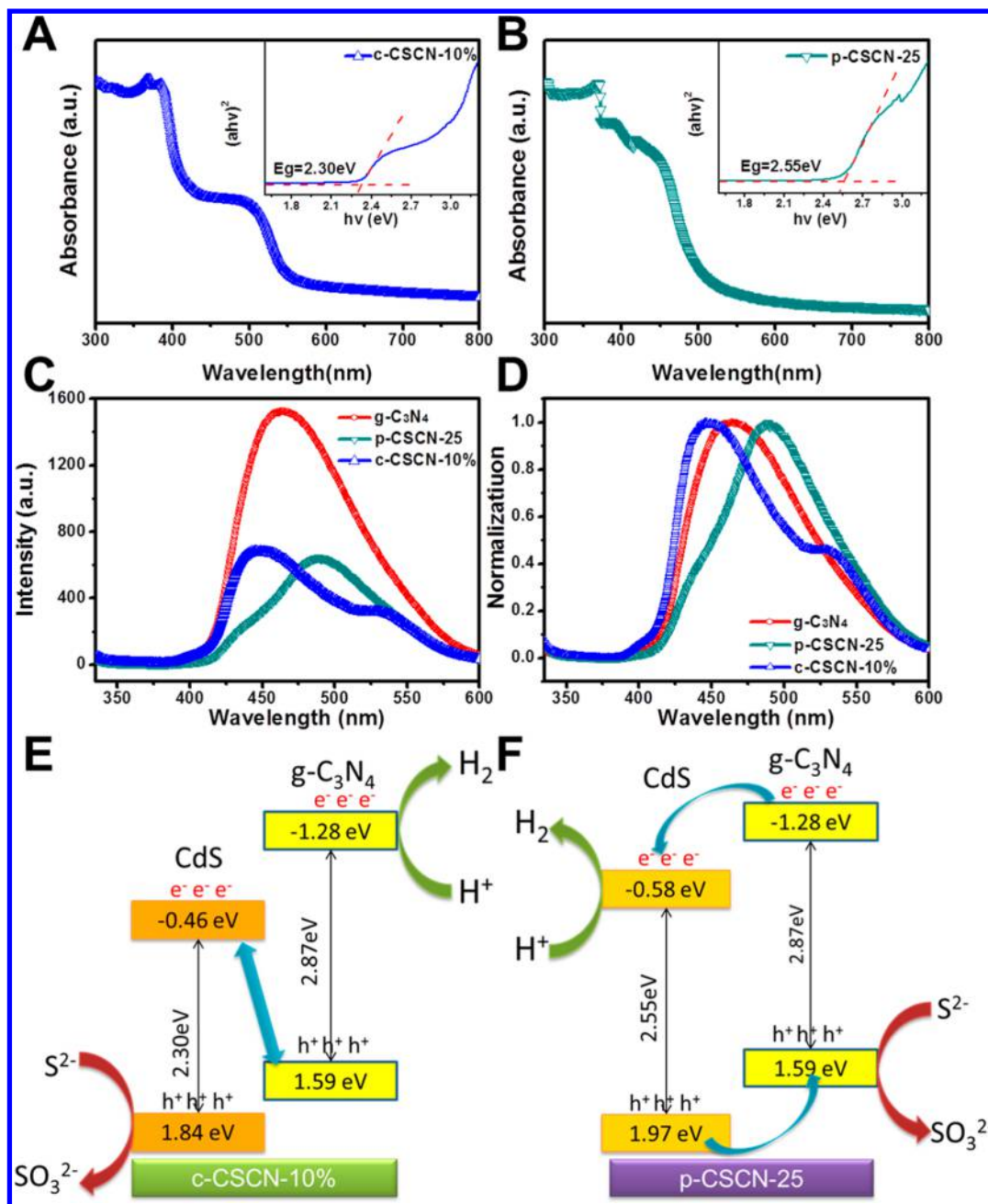


Figure 2. Optical properties of CSCN composites. UV-vis spectra and Tauc plots of $(\alpha h\nu)^2$ vs photon energy for band gap calculations of c-CSCN-10% (A) and p-CSCN-25 (B). Photoluminescence (PL, C) and normalized PL (D) spectra of g-C₃N₄, c-CSCN, and p-CSCN. Energy level diagrams and charge transfer routes of c-CSCN-10% (E) and p-CSCN-25 (F).

To prove our concept, the energy level diagram was calculated and measured. From the UV-vis spectra of g-C₃N₄, CdS, and CdS/g-C₃N₄ composite (Figure S2), the optical band gap can be obtained from a transformed Kubelka-Munk function (Figure 2A,B insets): 2.87 eV for g-C₃N₄, 2.30 eV for CdS in c-CSCN, and 2.58 eV for CdS in p-CSCN, respectively. In general, the CB and VB band edge positions of a semiconductor can be determined using a simple method.^{34,35} The conduction band (CB) edge of a semiconductor at zero charge can be determined using the equation

$$E_{\text{CB}} = \chi - E^{\circ} - 1/2E_{\text{g}} \quad (1)$$

$$E_{\text{VB}} = E_{\text{g}} + E_{\text{CB}} \quad (2)$$

where E_{CB} is the CB edge potential, E_{VB} is the valence band (VB) edge potential, and χ is the electronegativity of the semiconductor, expressed as the geometric mean of the absolute electronegativity of the constituent atoms, which is defined as the arithmetic mean of the atomic electron affinity and the first ionization energy. E° is the energy of free electrons on the hydrogen scale, ~ 4.5 eV, and E_{g} is the band gap of the semiconductor. According to the band gap of g-C₃N₄ of 2.87 eV, the calculated CB and VB of g-C₃N₄ are -1.28 and 1.59 eV vs NHE, respectively, which are close to those in Wang's report.³⁶ The band gaps of CdS in c-CSCN and p-CSCN are 2.30 and 2.58 eV, respectively. The calculated CB and VB are -0.46 and 1.84 eV for CdS in c-CSCN and -0.58 and 1.97 eV for CdS in p-CSCN. In addition, valence band X-ray

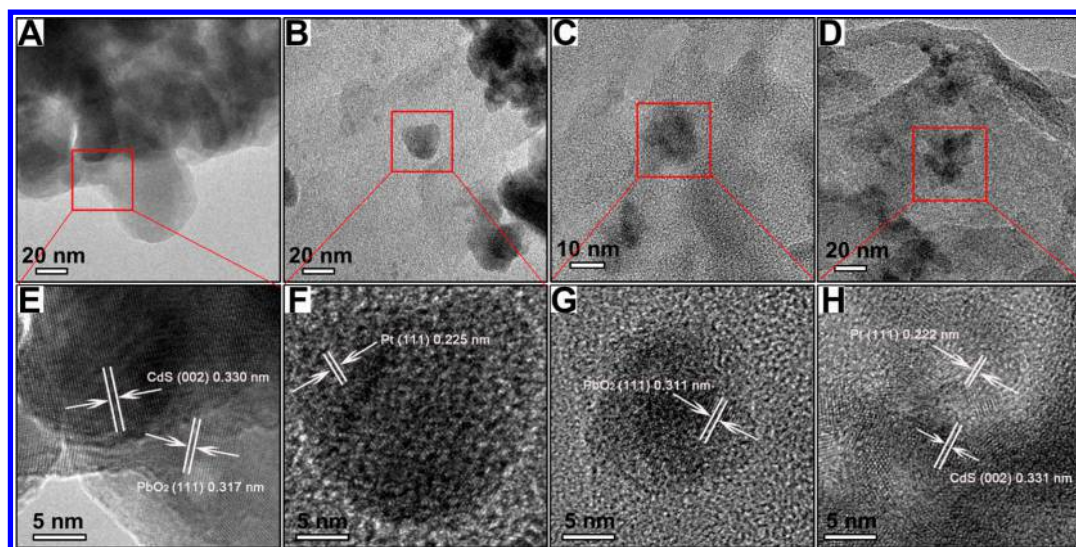


Figure 3. Charge transfer route of c-CSCN-10% and p-CSCN-25. TEM images of c-CSCN-10% (A, B, E, F) and p-CSCN-25 (C, D, G, H) photodeposited with PbO₂ nanoparticles (A, E, C, G) and Pt (B, F, D, H) nanoparticles. (E–H) give the corresponding high-resolution TEM images, respectively.

photoelectron spectroscopy (VB XPS) has been employed to verify the position of VB of the catalysts. Figure S3 illustrates the VB XPS spectra of g-C₃N₄, p-CSCN-25, and c-CSCN-10%. The VB of g-C₃N₄ is 1.49 eV, which is close to the calculated value. The VB of p-CSCN-25 is 1.55 eV, which is close to the VB of g-C₃N₄. This indicates that the holes rapidly transfer from CdS to g-C₃N₄. The VB of c-CSCN-10% is 1.79 eV, which is close to the VB of CdS. This implies that the holes are left on the CdS in c-CSCN. On the basis of these results, the energy level diagram of CdS/g-C₃N₄ and the charge transfer route are proposed and shown in Figure 2E,F.

Photoluminescence (PL) spectroscopy has been employed to characterize the charge transfer of CdS/g-C₃N₄ composites. As shown in Figure 2C, the PL intensity greatly decreases, indicating that the radiation recombination of g-C₃N₄ is depressed and charge separation is enhanced because of the formation of both Z-scheme and type II heterojunctions in the CdS/g-C₃N₄ composite. g-C₃N₄ shows a PL emission peak at ~464 nm (2.67 eV), which is smaller than the optical band gap of g-C₃N₄ (2.87 eV), in which the relaxation of an excited electron from the bottom of the CB to the sub-band (or surface state) and the radiative transition from the sub-band to the top of the VB subsequently lead to PL emission. In the case of c-CSCN, the maximum emission has a blue shift from ~464 to ~443 nm (2.80 eV), indicating that a new radiation recombination happens as in g-C₃N₄. The corresponding transition (2.80 eV) is about 0.13 eV greater than that of g-C₃N₄, indicating that the emission transition is not from pure g-C₃N₄. According to Yan's report, P3HT/g-C₃N₄ composites exhibited two new PL emission peaks at 375 and 720–750 nm in addition to emission from the individual g-C₃N₄ and P3HT. They assigned these two new PL emissions as the transition from the excited electron of P3HT with the hole of g-C₃N₄ and the recombination of the excited electron of g-C₃N₄ with the hole of P3HT.^{37–39} Zhou et al. also reported an indirect optical transition effect in the multilayer Ti_{0.91}O₂/CdS hollow spheres. PL spectra disclosed the recombination between the excited electron of Ti_{0.91}O₂ and the hole of CdS via d–p conjugation.^{25,40} Thus, we believe that the emission at 443 nm mainly comes from the recombination of the excited

electron of g-C₃N₄ with the hole from CdS. The emission at 525 nm is contributed by CdS. In the case of p-CSCN, there should be a peak at 440 nm and a red-shifted emission peak at 485 nm (Figure 2D). The former may be minor recombination, similar to the emission at 443 nm in c-CSCN. The major emission at 488 nm (2.52 eV) can be attributed to the transition from the CB to VB of CdS because it is close to the band gap (2.58 eV) of CdS. This transition contains not only an excited electron from CdS but also an excited electron transferred from g-C₃N₄. On the basis of PL results, we speculate the nature of the charge transfer route is as shown in Figure 2E,F.

To confirm the charge transfer route, the photodeposition of Pt and PbO₂ nanoparticles was carried out for both c-CSCN and p-CSCN. Generally, Pt nanoparticles, reduced from H₂PtCl₆ by acceptance of an electron, can be used for characterization of the site of photogenerated electron flow, and PbO₂, oxidized from Pb(NO₃)₂ by accepting hole, characterizes the hole transfer route.⁴¹ Figure 3A,E illustrate the TEM images of photodeposition of PbO₂ nanoparticles on c-CSCN. Figure 3E clearly exhibits that two connected particles with lattice fringe spacings of 0.330 and 0.317 nm are observed in the HR TEM images. They are assigned to the (002) plane of CdS and (111) plane of PbO₂, indicating that the PbO₂ nanoparticles were photodeposited onto the CdS particles. This implies hole transfer from CdS to PbO₂. Figure 3B,F gives the TEM images of Pt nanoparticle deposition. The HR TEM images show that the lattice fringe space is 0.225 nm, corresponding to the (111) plane of Pt. Also, there are no other particles surrounding the Pt nanoparticles, indicating that the Pt nanoparticles were directly deposited onto g-C₃N₄. This implies that the electron transfers from g-C₃N₄ to Pt nanoparticles. These results illustrate that the photogenerated electron remains at g-C₃N₄ and hole tends to be located at the site of CdS in c-CSCN-10% sample.

Figure 3C,D gives TEM images of the corresponding photodepositions of Pt and PbO₂ on p-CSCN-25. PbO₂ nanoparticles with a lattice fringe spacing of 0.311 nm were observed and existed separately on the g-C₃N₄ surface (Figure 3C,G). This implies that the hole transfers from g-C₃N₄ to the

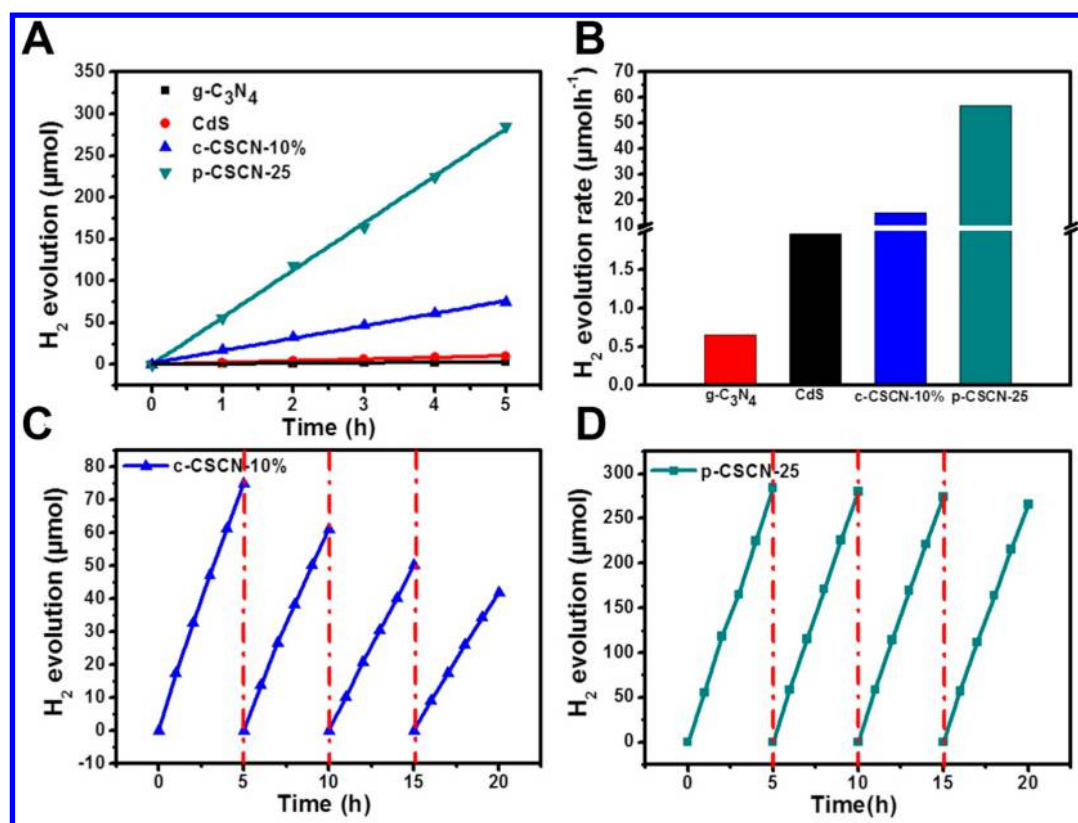


Figure 4. Photocatalytic performance of g-C₃N₄, CdS, c-CSCN-10%, and p-CSCN-25 and the composite photocatalyst stabilities. (A) Amount of H₂ generation of g-C₃N₄, CdS, c-CSCN-25, and p-CSCN-10% under visible light ($\lambda > 420$ nm) for 25 mg of the photocatalyst in 0.05 M Na₂S–0.1 M Na₂SO₃ aqueous solution for 5 h. (B) Their photocatalytic H₂ production rate. Cycling test of photocatalytic H₂ evolution for c-CSCN-10% (C) and p-CSCN-25 (D) composites with 1.0 wt % cocatalyst Pt nanoparticles. Conditions: light source, 300 W Xe lamp, $\lambda > 420$ nm; reaction solution, 100 mL of Na₂S (0.05 mol/L)–Na₂SO₃ (0.1 mol/L) aqueous solution; catalyst 25 mg.

site of PbO₂ nanoparticles, where the Pb²⁺ is oxidized by holes and forms PbO₂. However, the Pt nanoparticles with a lattice fringe spacing of 0.222 nm grow together with CdS nanoparticles (0.331 nm of lattice fringe space) (Figure 3D,H), implying that the electron transfers from CdS to Pt nanoparticles. In the case of p-CSCN, the photogenerated electron will be transferred from g-C₃N₄ to CdS and the hole remains at g-C₃N₄. These charge tracking results manifested that the photogenerated charge has entirely different transfer routes for c-CSCN and p-CSCN samples.

On the basis of the PL and charge tracking results, c-CSCN forms a Z-scheme type photocatalyst and p-CSCN is a type II heterojunction photocatalyst. The charge transfer directions are also displayed in Figure 1E,F.

To further confirm our proposal, photocatalytic performance and stability were investigated. H₂ production is a typical method to characterize the photocatalytic activity of a catalyst. As is well-known, Na₂S–Na₂SO₃ buffer solution is a common sacrificial agent for H₂ production for sulfide type photocatalysts to depress photocorrosion. Figure 4A,B exhibits the photocatalytic activities of g-C₃N₄, CdS, c-CSCN, and p-CSCN loaded with 1.0 wt % Pt nanoparticles in a Na₂S–Na₂SO₃ buffer solution, respectively. A 25 mg portion of g-C₃N₄ exhibits weak photocatalytic activity (0.65 $\mu\text{mol h}^{-1}$) under visible light irradiation ($\lambda > 420$ nm). For comparison, CdS prepared from a hydrothermal route shows the photocatalytic H₂ evolution rate of 1.96 $\mu\text{mol h}^{-1}$ for 25 mg of the photocatalyst. c-CSCN-10% shows a photocatalytic activity of 14.9 $\mu\text{mol h}^{-1}$, which is higher than that of any single component. In the case of p-

CSCN-25, the photocatalytic rate reaches 56.9 $\mu\text{mol h}^{-1}$, which is the highest among these samples. Figure 4C,D illustrates the durability of c-CSCN-10% and p-CSCN-25 samples. The stability of c-CSCN-10% and p-CSCN-25 was tested in Na₂S–Na₂SO₃ buffer solution for four times of repeated photocatalytic H₂ production. After four recycles, c-CSCN-10% had a serious loss of activity ($\sim 50\%$), implying that the catalyst c-CSCN-10% was photocorroded during the H₂ production. Normally, photocorrosion happens due to the sulfide being oxidized by holes. It can be depressed by rapidly transferring the holes away from the sulfide. In contrast, p-CSCN-25 showed much better stability during the photocatalytic H₂ evolution. This is a clear sign that holes are transferred away from the sulfide. To confirm this speculation, triethanolamine (TEOA) was also used as a sacrificial agent to test the photocatalytic activity and stability, as shown in Figure S9. CdS exhibits worse stability in the first 5 h test in comparison to that in the Na₂S–Na₂SO₃ buffer solution due to photocorrosion. Although the photocatalytic activities of c-CSCN-10% and p-CSCN-25 are lower than those in the Na₂S–Na₂SO₃ system, p-CSCN-25 still exhibits the best photocatalytic activity and excellent stability among all the samples. Since p-CSCN shows super stability, this is strong evidence that the hole might be transferred away from the CdS site.

On the basis of the UV–vis spectra (Figure S2), although the c-CSCN shows broader light absorption, the overall photocatalytic activity of c-CSCN is worse than that of p-CSCN. To understand these results, the wavelength dependence of the H₂ evolution rate was investigated for c-CSCN and p-CSCN.

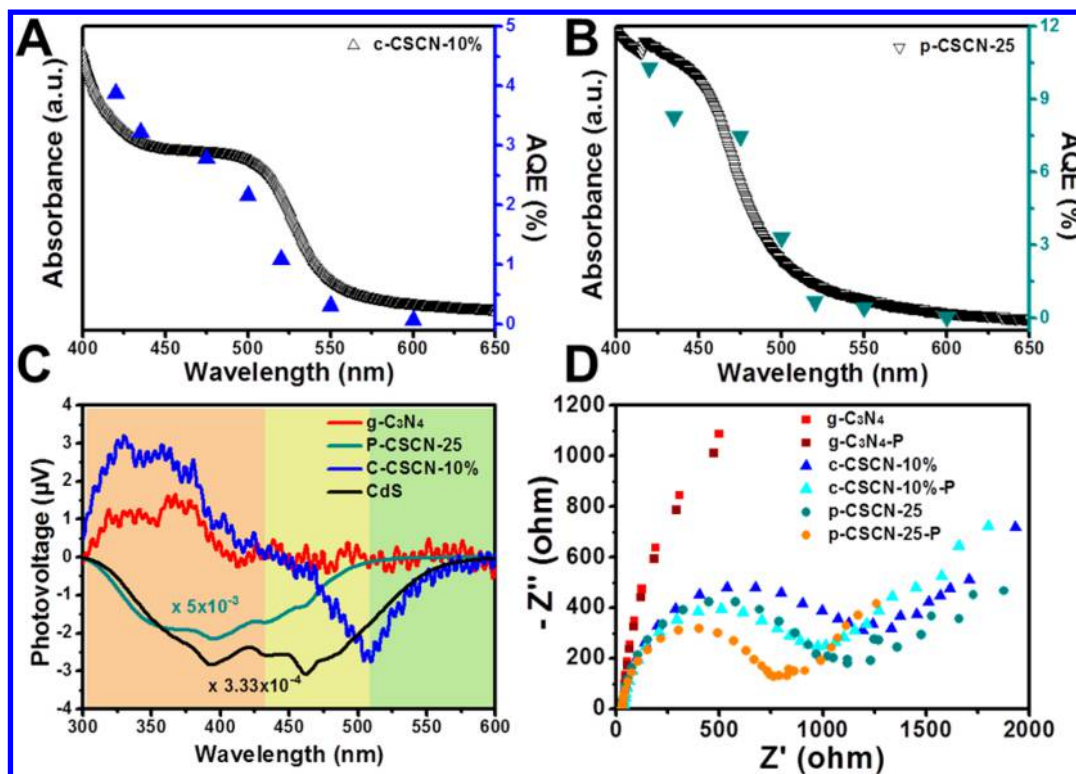


Figure 5. Apparent quantum efficiency and UV-vis spectra of c-CSCN (A) and p-CSCN (B). (C) Surface photovoltage spectra of g-C₃N₄, CdS, p-CSCN-25, and c-CSCN-10%. The signal intensity of CdS and p-CSCN-25 was divided by 3000 and 200 to fit into the plot. (D) Electrochemical impedance spectroscopy (EIS) of g-C₃N₄, c-CSCN, and p-CSCN with/without light irradiation (P).

Figure 5A,B shows the apparent quantum efficiency (AQE) vs wavelength plot together with the UV-vis absorption spectra of c-CSCN-10% and p-CSCN-25, respectively. In both cases, the change in AQE follows the change in absorption spectra. For the c-CSCN-10% sample, the AQE is about 3.8% at 420 nm, reaches a plateau in the range from 430 to 500 nm, and then decreases quickly to 0.3% at 550 nm. In the case of p-CSCN-25, the AQE is about 10.3% at 420 nm, which is much higher than that of c-CSCN, and the AQE maintains a short plateau from 430 to ~475 nm (>7.5%) and then quickly decreases to 0.7% at 520 nm. The AQE trend fully matches with the light absorption in both cases. However, AQE indicates that the light conversion efficiency of p-CSCN is higher than that of c-CSCN. When photocatalytic activity and light absorption are considered, it is possible that the charge separation efficiency in p-CSCN is much better than that in c-CSCN.

To investigate the charge transfer efficiency, the surface photovoltage spectroscopy (SPS) of CdS/g-C₃N₄ composite nanosheets was investigated in comparison with those of pure g-C₃N₄ and CdS. As shown in Figure 5C, a poor response appears on the SPS curve of pure g-C₃N₄ nanosheets, indicating very low efficiency in the photovoltaic conversion. It shows an obvious positive photovoltage response in the range of 300–440 nm for pure g-C₃N₄, which is the typical feature of an n-type semiconductor.^{38,42,43} The low photovoltage of g-C₃N₄ can be attributed to the Schottky interface contact between g-C₃N₄ and ITO glass in the absence of electrolyte, which leads to a limited electron transfer process from g-C₃N₄ to the ITO glass electrode. In contrast, CdS exhibited relatively strong negative SPS response, whose intensity was divided by 3000, corresponding to the high charge separation rate.⁴⁴ A negative

photovoltage signal indicates electron transfer toward the metal substrate. Its photovoltage response fully matches with its UV-vis spectrum ranging from 300 to 600 nm. After loading with CdS on g-C₃N₄, the SPS signals of composites are stronger than that of g-C₃N₄, indicating the charge separation of composites is more efficient than that of g-C₃N₄. In the case of p-CSCN, the photogenerated electron transfers from g-C₃N₄ to CdS due to the formation of a type II heterojunction; thus, the SPS signal is negative, which is similar to the signal of CdS. In the case of c-CSCN, the SPS signal covers from 300 to 600 nm because CdS has broader light adsorption in c-CSCN. The negative SPS signal is observed in the long-wavelength region because g-C₃N₄ has no absorption and only CdS absorbs light in this region. In the middle-wavelength region, a weak light adsorption from defects of g-C₃N₄ (positive signal) and light absorption from CdS (negative signal) lead to the decreased signal of CdS. With the light absorption enhancement of g-C₃N₄, the formation of a Z-scheme species results in more electrons being kept at the g-C₃N₄; thus, the SPS signal turns positive, which is similar to the case for pure g-C₃N₄. For p-CSCN, the photovoltage response starts from 300 to 480 nm and is negative, which means that the electrons stay on the CdS and follow the behavior of pure CdS. It should be noted that the SPS signal was divided by 200 in order to fit into the plot. This indicates that the charge separation efficiency is much better than those of g-C₃N₄ and c-CSCN.

Furthermore, transient photocurrents of samples were measured during repeated ON/OFF illumination cycles at 0.2 V bias voltage. All samples exhibit reproducible photocurrent response on each illumination (Figure S10). When the light was on, the photocurrent rapidly jumped up and reached a stable value, and the photocurrent dropped to the baseline

when the irradiation was interrupted. The transient photocurrent density of p-CSCN-25 is more than $0.64 \mu\text{A cm}^{-2}$, whereas those of c-CSCN-10% and g-C₃N₄ are ~ 0.4 and $0.24 \mu\text{A cm}^{-2}$, respectively. The photocurrent density of p-CSCN is larger than those of c-CSCN and g-C₃N₄. These results confirm that composite photocatalysts have better charge separation efficiency in comparison to g-C₃N₄ and that p-CSCN has better charge separation efficiency in comparison to c-CSCN.

It is commonly known that electrochemical impedance spectroscopy (EIS) analysis provides information about the interfacial properties of electrodes. The diameter of the semicircle in EIS is related to the electron transfer resistance, which brings out electron transfer kinetics of the redox probe at the electrode/electrolyte interface. In the equivalent circuit (Figure S11), R_s is the series resistance, CPE is the constant phase element for the electrolyte/electrode interface, and R_p is the charge transfer resistance across the electrode/electrolyte interface. In general, the smaller the radius of the semicircle, the smaller the charge transfer resistance, denoting faster separation and transfer of the photogenerated electron–hole pairs.⁴⁵ As shown in Figure 5D, the large arc radius of pure g-C₃N₄ may be caused by poor electrical conductivity and high resistance of the C–N network. The radius of the semicircles decreases significantly after incorporation of the CdS particles. The R_p value dramatically decreases from 3260 to 1030 Ω for c-CSCN-10% and 793 Ω for p-CSCN-25, respectively. These confirm that the p-CSCN-25 has best charge transfer efficiency. Under light irradiation, the radius of the semicircle turns smaller in comparison with dark cases. This indicates that the light irradiation will enhance the charge separation and transfer. On the basis of the above results, although p-CSCN has narrower light adsorption, it has a more efficient charge separation process in comparison to c-CSCN. This is the reason p-CSCN has better H₂ production activity.

Although both c-CSCN and p-CSCN have the same composition of CdS and g-C₃N₄, they build up different types of composites, a type II heterojunction and Z-scheme, due to the different synthesis routes. For p-CSCN, the photodeposition is a light-induced reduction reaction and the CdS is grown at an active site at which an electron is ready to transfer onto g-C₃N₄. This is why p-CSCN tends to transfer electrons from g-C₃N₄. Thus, by regulating the electron flow direction, we can construct heterojunction type photocatalyst. In the case of c-CSCN, the chemical deposition sites of CdS are randomly dispersed on g-C₃N₄, because it is in the reaction solution. The electron from g-C₃N₄ does not prefer to flow toward CdS. The excited electron of CdS has a great opportunity to combine with the hole of g-C₃N₄ and create the Z-scheme type catalyst. In this report, we start from g-C₃N₄ (PSII) and deposit CdS (PSI) via a photoreduction reaction, and a type II heterojunction catalyst is obtained. If we start from PSII and deposit PSI via a photo-oxidation reaction, a Z-scheme type catalyst will be formed.

CONCLUSIONS

In summary, we built up two composites from CdS and g-C₃N₄ via photodeposition and chemical hydrothermal routes. These two composites exhibit different photocatalytic activities and stabilities. From tracking of the charge flow direction and PL spectroscopy, the electron tends to transfer from g-C₃N₄ to CdS and the hole goes to g-C₃N₄ to form a type II heterojunction in the case of p-CSCN. In contrast, the electron tends to remain at g-C₃N₄ and the hole stays at CdS and creates

a direct Z-scheme species. SPS spectra, EIS spectroscopy, and AQE results indicate that the charge separation of p-CSCN is more efficient than that of c-CSCN in the CdS/g-C₃N₄ composites. For an analysis of the reason, p-CSCN was synthesized from photodeposition of CdS on g-C₃N₄, which is a photogenerated electron induced reduction reaction on the surface of g-C₃N₄. This indicates that the photogenerated electron highly prefers to flow from g-C₃N₄ to CdS. However, as c-CSCN is produced by chemical reduction deposition, there no preferred site for the photogenerated electron. These results demonstrated that photodeposition could be used for the regulation of photogenerated charge flow direction. Furthermore, it can be used for constructing a direct Z-scheme and/or type II heterojunction. This report may open the door to regulate Z-scheme and type II heterojunction and judge the composite form as being a type II heterojunction or Z-scheme.

EXPERIMENTAL SECTION

Synthesis of the Photocatalysts. All chemicals were analytical grade and were used without further purification.

Preparation of g-C₃N₄.³⁰ Graphitic carbon nitride (g-C₃N₄) powder was synthesized by the pyrolysis of urea. A 50 g portion of urea was put into an alumina crucible with a cover and then heated to 550 °C for 3 h in a muffle furnace at a temperature rate of 0.5 °C/min.

Preparation of Photodeposited CdS/g-C₃N₄ (p-CSCN).⁴⁶ The sample of p-CSCN was prepared by photodeposition. Sulfur (2 mmol) and Cd(NO₃)₂·4H₂O (8 mmol) were added to 200 mL of an ethanol suspension containing 200 mg of g-C₃N₄. This suspension was irradiated with a 300 W Xe lamp for 5 h under different temperatures of circulating water. Then the solid product was collected by centrifugation and washed several times with deionized water, ethanol, and carbon disulfide (CS₂) to remove unreacted raw materials such Cd(NO₃)₂ and S powder. The samples produced at temperatures of 4, 25, and 50 °C were dried in the oven at 60 °C overnight and denoted p-CSCN-4, p-CSCN-25, p-CSCN-50, respectively.

Preparation of Chemical-Deposited CdS/g-C₃N₄ (c-CSCN).³² The sample of c-CSCN was produced by chemical deposition. A 0.35 mmol portion of Cd(NO₃)₂·4H₂O and 1.503 g of thioacetamide (TAA) were added to 60 mL of deionized water containing 0.5 g of as-prepared g-C₃N₄. The achieved suspension was ultrasonicated for 30 min and subsequently transferred into a 100 mL Teflon-lined stainless steel autoclave, and then it was heated to 160 °C and kept at this temperature for 5 h. The obtained sample was washed several times with deionized water and ethanol, dried in the oven at 60 °C, and denoted by c-CSCN-10%. The others c-CSCN samples were synthesized by a similar method by changing the amount of Cd(NO₃)₂·4H₂O. These samples according to the weight ratio of g-C₃N₄ and CdS are denoted c-CSCN-1% (0.035 mmol of Cd(NO₃)₂·4H₂O), c-CSCN-5% (0.175 mmol of Cd(NO₃)₂·4H₂O), c-CSCN-10% (0.35 mmol of Cd(NO₃)₂·4H₂O), and c-CSCN-15% (0.525 mmol of Cd(NO₃)₂·4H₂O), respectively. The pure CdS photocatalyst was obtained under the same conditions without adding g-C₃N₄ powder.

Characterizations. The crystal structures of the samples were investigated using X-ray diffraction (XRD; Bruker D8 Advance X-ray diffractometer) with Cu K α radiation (λ = 0.15406 nm) as the incident beam at 40 kV and 40 mA. The morphologies of the samples were examined by transmission

electron microscopy (TEM; FEI Tecnai G2 F20) operated at 200 kV and scanning electron microscopy (SEM; JEOL S-4800) operated at 5 kV. UV–vis diffuse reflection spectroscopy (DRS) was performed on a Shimadzu UV-2600 spectrophotometer using BaSO₄ as the reference. The photoluminescence (PL) spectra of the photocatalyst were obtained by a Hitachi F-7000 instrument with an excitation wavelength of 325 nm. The BET specific surface area was measured using a Quantachrome Surface Area and Pore Size Analyzer (Quantachrome Instruments version 3.01). Electrochemical measurements were conducted with an Autolab PGSTAT302N instrument in a conventional three-electrode cell, using a carbon electrode as the counter electrode and an Ag/AgCl electrode as the reference electrode. The working electrode⁴⁷ was prepared on FTO glass that had been cleaned by sonication in ethanol for 30 min and dried at 100 °C. The 20 mg of the sample was dispersed in 100 mL of a 0.2 mg mL^{−1} I₂/acetone solution under ultrasonic treatment. A two-electrode process was used to deposit the samples at an applied potential of 10 V for 3 min. FTO glass substrates with a coated area of about 1 × 1 cm² were used for both electrodes. Then, the deposited electrode was dried at 300 °C for 60 min to remove residual I₂.

Photocatalytic Hydrogen Evolution. Photocatalytic hydrogen evolution via water splitting was performed in a closed Pyrex glass reactor. For investigations of photocatalytic performance, the well-ground photocatalyst (10 mg) was suspended in Na₂S (0.05 M) and Na₂SO₃ (0.1 M) aqueous solution (100 mL) under vigorous stirring. A 1 wt % amount of Pt was photodeposited onto the catalysts using H₂PtCl₆ dissolved in the reactant solution. A 300 W Xe lamp was also utilized as the visible light source for irradiation with a 420 nm cutoff filter for the photocatalytic reactions. The temperature of the reactant solution was maintained at 0 °C by a flow of a cycle cooling water system during the reaction. The amount of hydrogen produced was determined by gas chromatography (Shimadzu GC-2014C), using a thermal conductivity detector (TCD) with N₂ as the carrier gas. Wavelength-dependent H₂ evolution measurement was also operated in the H₂ production system with band-pass filters for 420, 435, 475, 500, 520, 550, and 600 nm, respectively. The apparent quantum efficiency (AQE) was estimated using the equation

$$\text{AQE (\%)} = \frac{2 \times \text{number of evolved H}_2 \text{ molecules}}{\text{number of incident photons}} \times 100\%$$

The stability tests of the as-prepared composite materials (25 mg) of p-CSCN-25 and c-CSCN-10% were operated in the H₂ production system using Na₂S (0.05 M)/Na₂SO₃ (0.1 M) aqueous solution and 10 vol % triethanolamine (TEOA) aqueous solution as an electron donor.

Charge Flow Tracking by Photodeposition.⁴⁸ Photodeposition of 1 wt % Pt and PbO₂ on the surfaces of p-CSCN-25 (c-CSCN-10%) were carried out using H₂PtCl₆ and Pb(NO₃)₂ as precursors, respectively. Typically, 10 mg of p-CSCN-25 (c-CSCN-10%) and a calculated amount of the metal precursor were mixed in 100 mL of deionized water with stirring. The suspension was then irradiated by a 300 W Xe lamp with the reaction temperature maintained at 0 °C by cycle cooling water equipment. After 2 h of photodeposition, the suspension was filtered, washed several times with deionized water, and finally dried in the oven at 60 °C overnight. For photodeposition of Pt and PbO₂, Na₂S/Na₂SO₃ (molar ratio of

1/2) aqueous solution and 0.1 M NaIO₃ aqueous solution were used as electron donors and acceptors, respectively.

■ ASSOCIATED CONTENT

● Supporting Information

The Supporting Information is available free of charge on the ACS Publications website at DOI: 10.1021/acscatal.7b04323.

Optical photography, UV–vis, TEM, XRD, H₂ production, N₂ sorption, SEM, photocurrent and electrochemical impedance spectroscopy (PDF)

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Notes

The authors declare no competing financial interest.

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